

ABSTRACT OF DISCLOSURE

A method for fabricating a semiconductor device wherein an interconnect made of copper overlying a substrate is pretreated at a specified temperature, for example, at 300 °C or less; and a dielectric film is formed on the copper at a temperature higher than that of the pretreatment. In accordance with the present invention, the adhesion between the copper and the dielectric film is improved by conducting the pretreatment of the dielectric film for reducing an oxide layer of the copper surface, and the agglomeration of the copper can be prevented by the pretreatment.